

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph bridging pages 1-2 of the specification with the following amended paragraph:

Conventionally, p-conduction-type GaN for fabricating a pn-junction gallium nitride semiconductor light-emitting device is formed so that GaN contains an additive. For example, there has been disclosed a technique in which a Group II impurity, such as magnesium (Mg) or zinc (Zn), is added to a GaN layer through ion injection means (see, for example, ~~JP-A SHO 51-71590 JP-A SHO 54-71590~~).